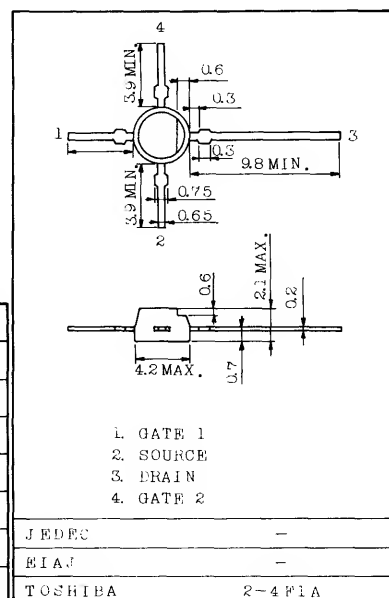


3SK121

Unit in mm

- . Superior Cross Modulation Performance
- . Low Reverse Transfer Capacitance ; $C_{RSS}=20\text{fF}$ (Typ.)
- . Low Noise Figure : $NF=1.5\text{dB}$ (Typ.)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	V_{DS}	10	V
Gate1-Source Voltage	V_{G1S}	-6	V
Gate2-Source Voltage	V_{G2S}	-6	V
Drain Current	I_D	50	mA
Power Dissipation	P_D	200	mW
Channel Temperature	T_{ch}	125	°C
Storage Temperature Range	T_{stg}	-55~+125	°C



Weight : 0.08g

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate1 Leakage Current	I _{G1SS}	V _{DS} =0, V _{G1S} =-5V, V _{G2S} =0	-	-	20	μA
Gate2 Leakage Current	I _{G2SS}	V _{DS} =0, V _{G1S} =0, V _{G2S} =-5V	-	-	20	μA
Drain-Source Current	I _{DSX}	V _{G1S} =-5V, V _{G2S} =-5V V _{DS} =10V	-	-	100	μA
Drain Current	I _{DSS} (Note)	V _{DS} =5V, V _{G1S} =0, V _{G2S} =0	20	-	45	mA
Gate1-Source Cut-off Voltage	V _{G1S(OFF)}	V _{DS} =5V, V _{G2S} =0, I _D =100μA	-	-2.5	-4	V
Gate2-Source Cut-off Voltage	V _{G2S(OFF)}	V _{DS} =5V, V _{G1S} =0, I _D =100μA	-	-2.5	-4	V
Forward Transfer Admittance	Y _{fS}	V _{DS} =5V, V _{G2S} =0 I _D =10mA, f=1kHz	-	17	-	mS
Input Capacitance	C _{iSS}	V _{DS} =5V, V _{G2S} =0	-	0.9	2.0	pF
Reverse Transfer Capacitance	C _{rSS}	I _D =10mA, f=1MHz	-	0.02	0.05	pF
Power Gain	G _{PS}	V _{DS} =5V, V _{G2S} =1V, I _D =10mA, f=800MHz	16	20.5	-	dB
Noise Figure	NF		-	1.5	2.5	dB

Marking

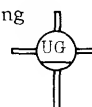
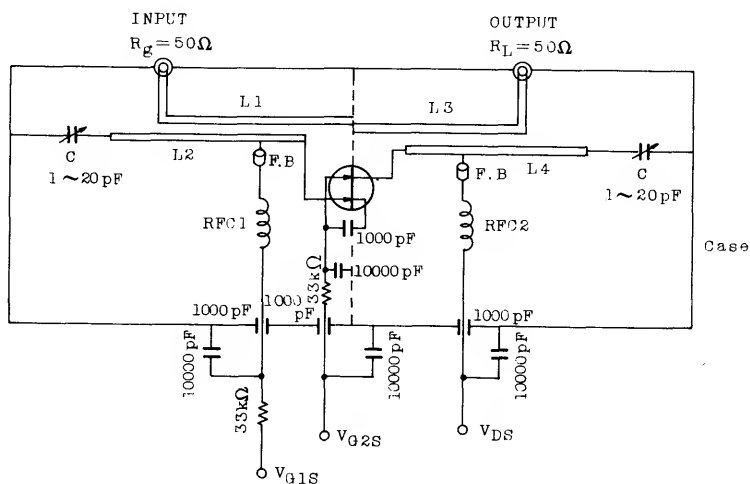


Fig. 1 800MHz Gps, NF TEST CIRCUIT



L1 ~ L4 : 1.0mm ϕ SILVER PLATED COPPER WIRE

C : AIR TRIMMER TTA25A200A (MURATA MFG. Co., LTD.)

RFC1 : 0.35mm ϕ COPPER WIRE 3mm ID, 7T

RFC2 : 0.35mm ϕ COPPER WIRE 3mm ID, 10T

